

1. General description

Planar passivated high commutation three quadrant triac in a ITO220 internally insulated plastic package. This triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers. This "series ET" triac will commute the full rated RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ °C}$) without the aid of a snubber.

2. Features and benefits

- High voltage capability
- High commutation capability with maximum false trigger immunity
- Direct interfacing with low level power drivers and logic ICs
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Sensitive gate for easy logic level triggering
- RoHS compliant
- Epoxy package meets UL94V-0 which guaranteed by epoxy molding compound
- Isolated package ($V_{iso} = 2500\text{ V}_{RMS}$)

3. Applications

- Compressor starting control circuits
- General purpose motor controls
- Reversing induction motor controls e.g. vertical axis washing machines
- Applications subject to high temperature ($T_{j(max)} = 150\text{ °C}$)

4. Quick reference data

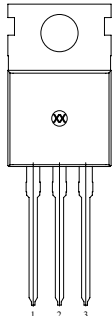
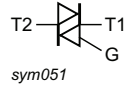
Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
V_{DRM}	repetitive peak off-state voltage			800			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 124\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3		8			A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5		60			A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$		65			A
T_j	junction temperature			150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7		-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7		-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7		-	-	10	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	-	30	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	1.30	1.65	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	400	-	-	V/ μ s
		$V_{DM} = 536\text{ V}$; $T_j = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/ μ s
dI_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 150\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit	3	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_j = 150\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	4	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_j = 150\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	6	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA308Y-800ET	IITO220	BTA308Y-800ETQ	Tube	50	IITO220P	31-Mar-2023

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA308Y-800ET	BTA308Y 800ET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 124\text{ °C}$; Fig.1 ; Fig.2 ; Fig.3		8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig.4 ; Fig.5		60	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$		65	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine wave pulse		18	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 70\text{ mA}$		100	$A/\mu s$
I_{GM}	peak gate current			2	A
P_{GM}	peak gate power			5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		0.5	W
T_{stg}	storage temperature			150	$^{\circ}C$
T_j	junction temperature			150	$^{\circ}C$

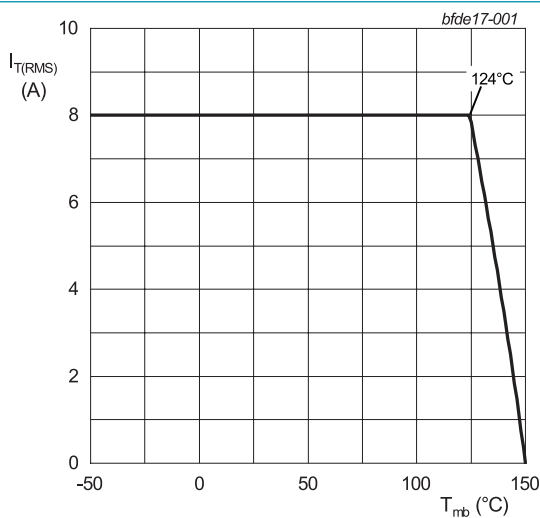
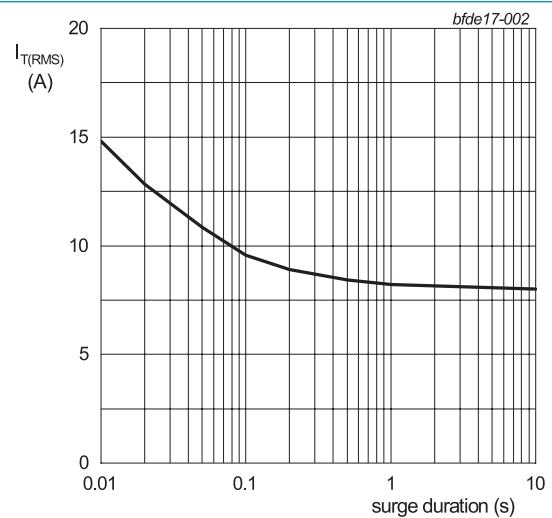
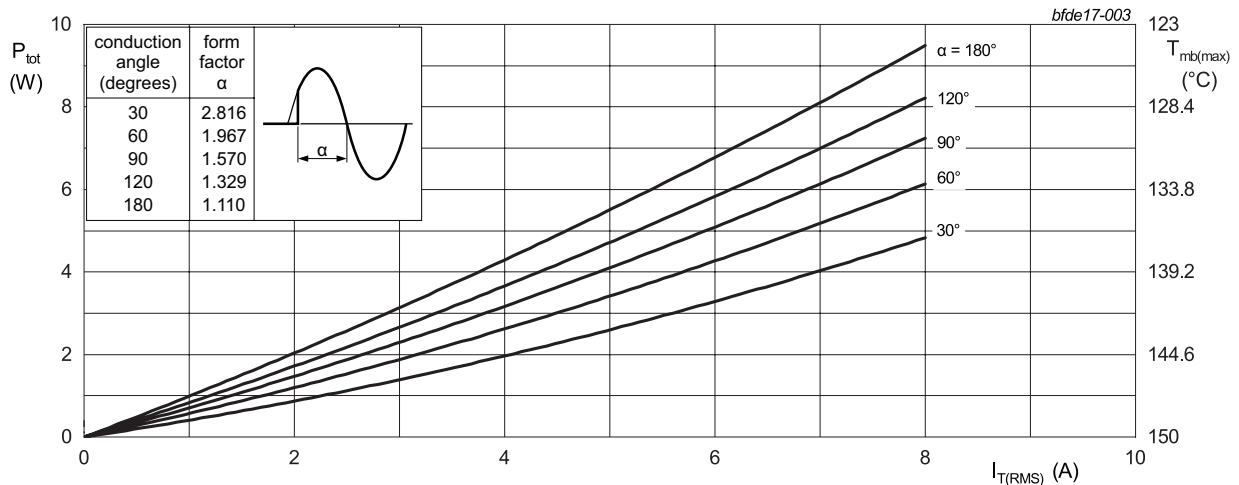


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

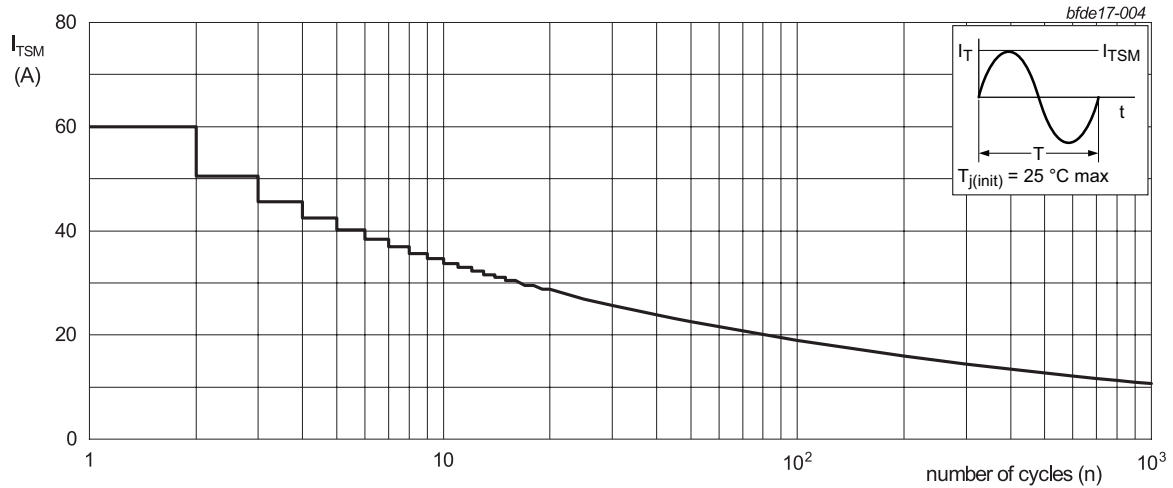


$f = 50\text{ Hz}$; $T_{mb} = 124\text{ °C}$
Fig. 2. RMS on-state current as a function of surge duration; maximum values



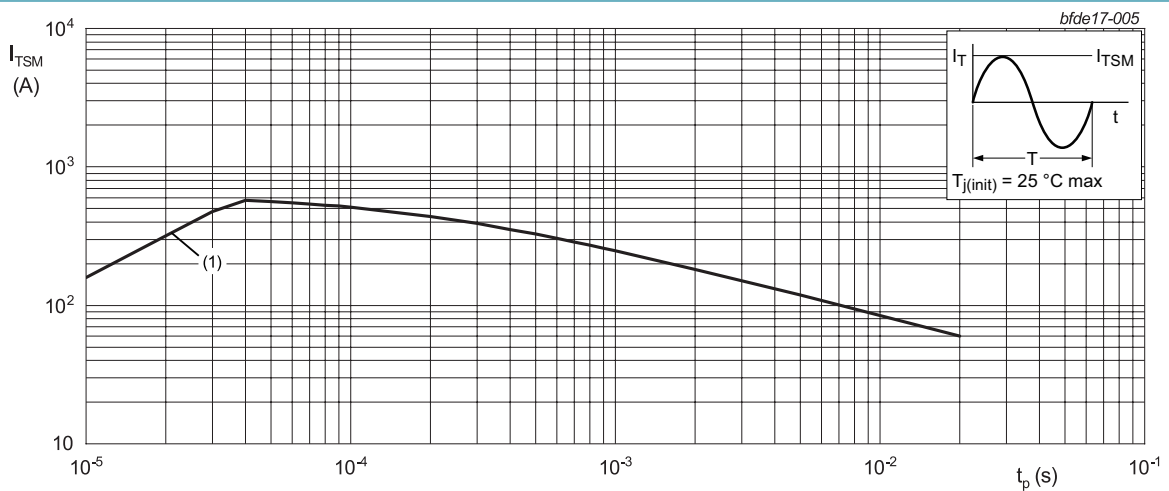
$a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$
 $\alpha = \text{conduction angle}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



$f = 50 \text{ Hz}$

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20 \text{ ms}$
 (1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 6		-	-	2.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

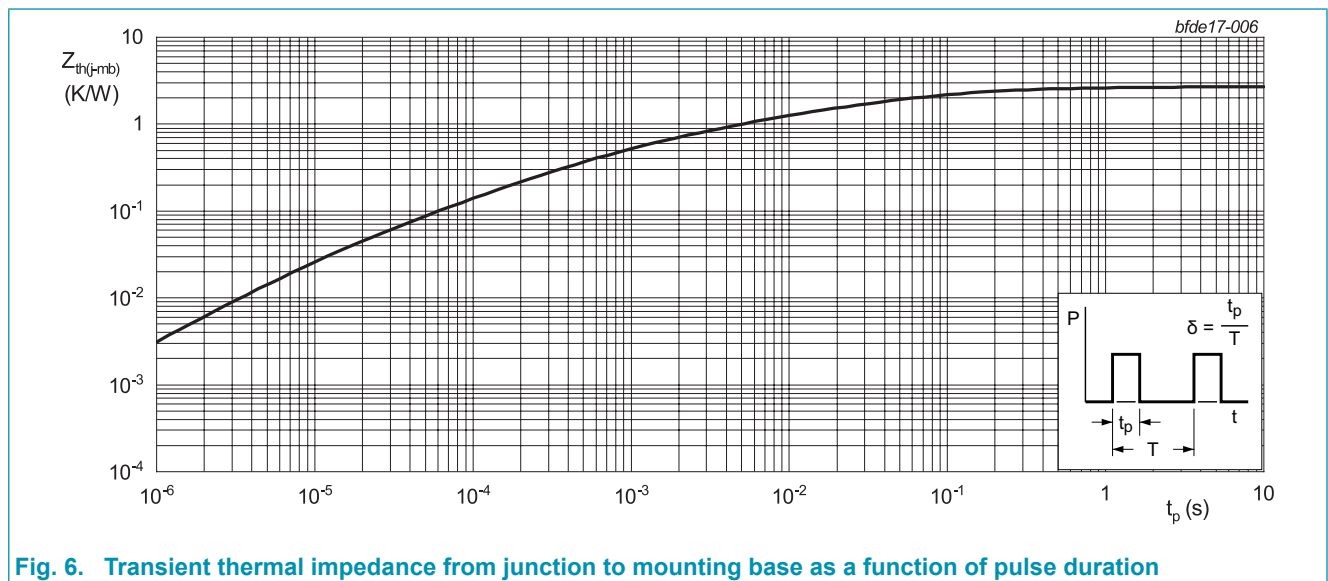


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Isolation characteristics

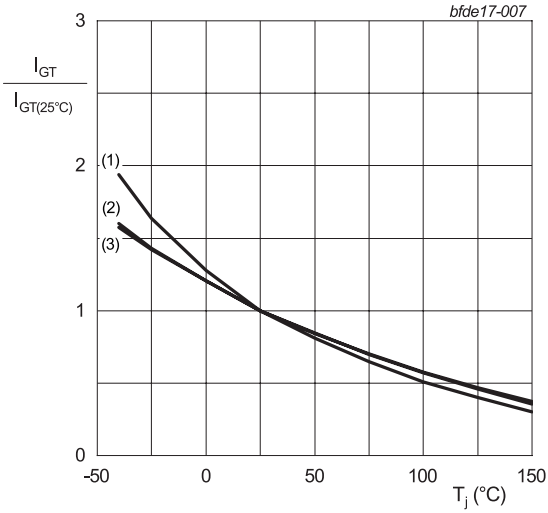
Table 7. Isolation Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq f \leq$ 60 Hz; RH \leq 65 %; $T_{mb} = 25$ °C		-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; $f = 1$ MHz; $T_{mb} = 25$ °C		-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 7		-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 7		-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 7		-	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 8		-	-	50	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 8		-	-	75	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 8		-	-	50	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ °C}$; Fig. 9		-	-	30	mA
V_T	on-state voltage	$I_T = 17\text{ A}$; $T_J = 25\text{ °C}$; Fig. 10		-	1.30	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ °C}$ Fig. 11		-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 150\text{ °C}$		0.2	0.45	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_J = 25\text{ °C}$		-	-	10	μA
		$V_D = 800\text{ V}$; $T_J = 150\text{ °C}$		-	-	0.5	mA
I_R	reverse current	$V_D = 800\text{ V}$; $T_J = 25\text{ °C}$		-	-	10	μA
		$V_D = 800\text{ V}$; $T_J = 150\text{ °C}$		-	-	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		400	-	-	V/ μs
		$V_{DM} = 536\text{ V}$; $T_J = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		200	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit		3	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit		4	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit		6	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

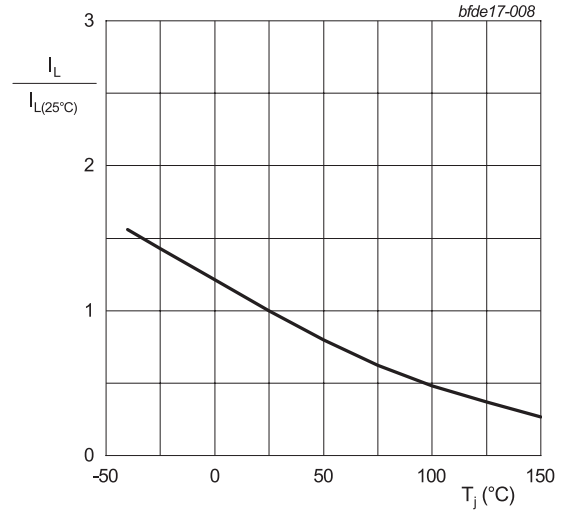


Fig. 8. Normalized latching current as a function of junction temperature

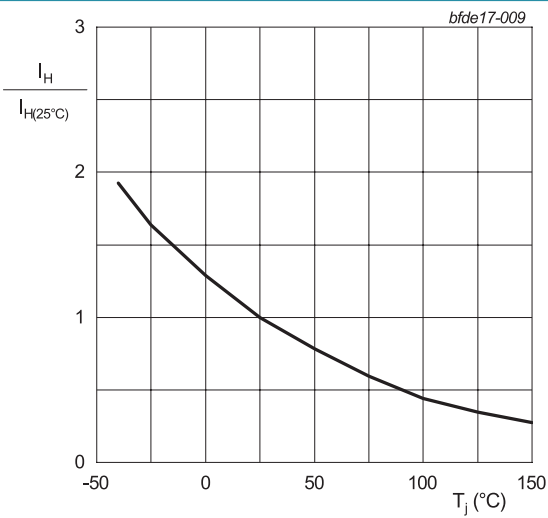
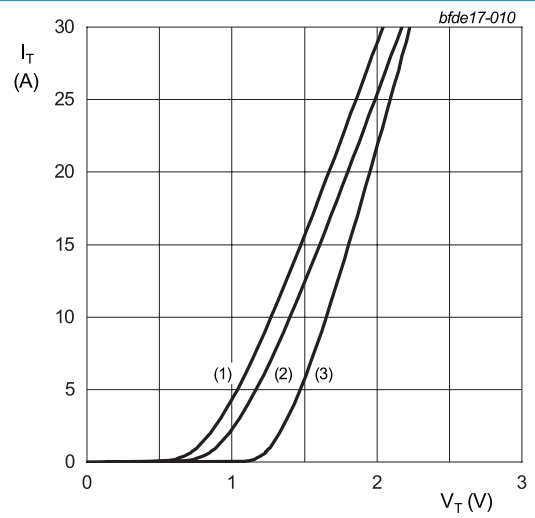


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.067 \text{ V}; R_s = 0.0281 \Omega$
- (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 - (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 - (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

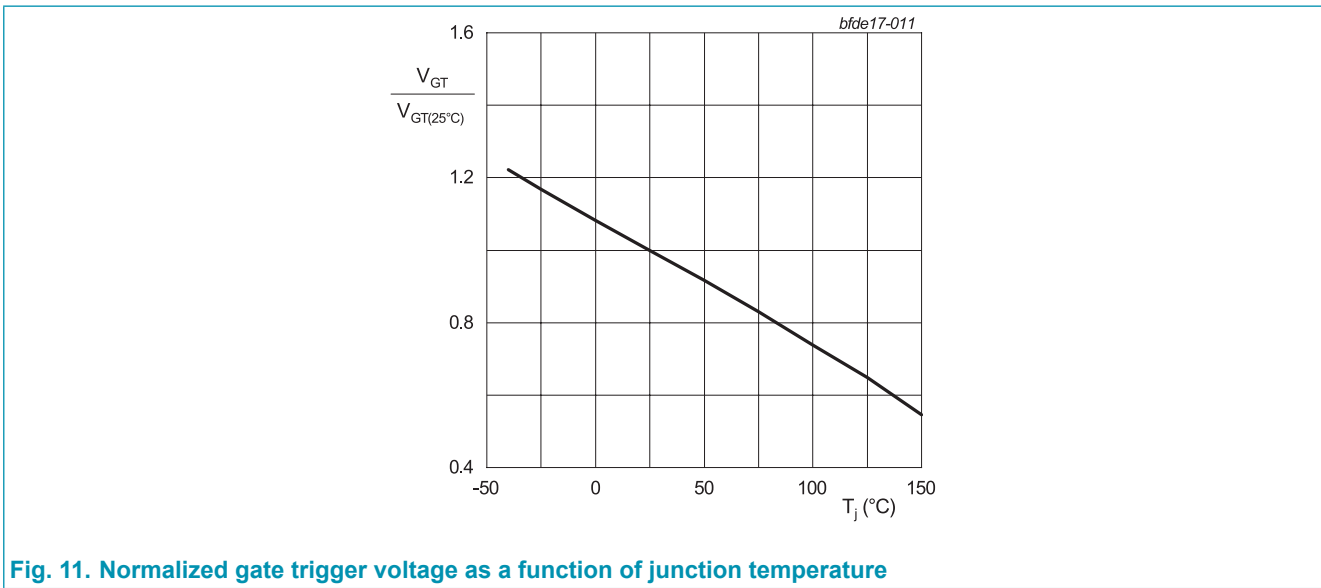
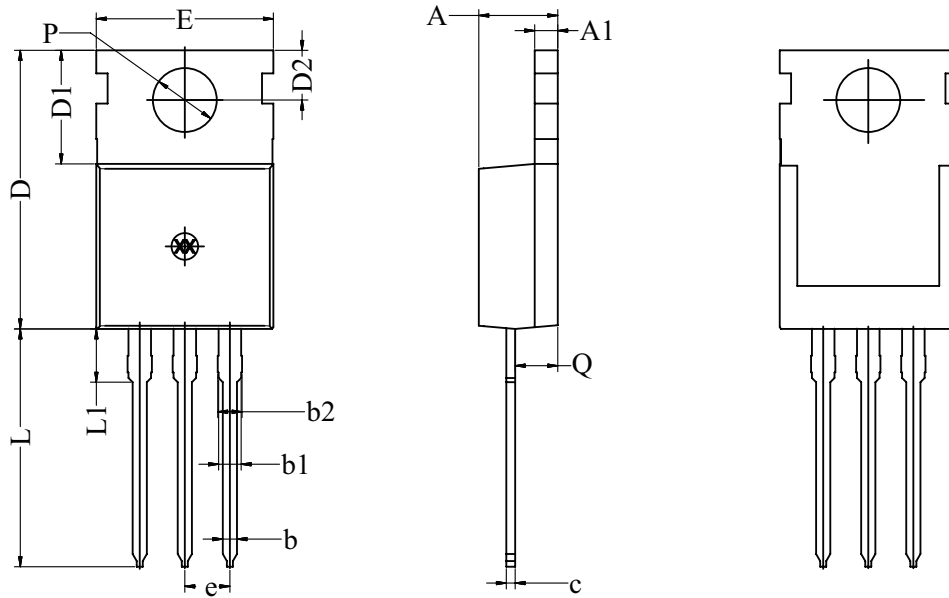


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3 leads TO-220

IIT0220



Dim	All Dimensions in Millimeters		
	Min	Typ	Max
A	4.30	4.45	4.70
A1	1.25	1.30	1.40
b	0.60	0.80	0.90
b1	1.10	1.27	1.40
b2	1.32	1.37	1.72
c	0.40	0.50	0.60
D	15.20	15.70	16.00
D1	6.20	6.40	6.60
D2	2.70	2.80	3.00
E	9.70	10.00	10.30
e	2.54 BSC		
L	12.80	13.40	14.00
L1	2.80	3.00	3.20
P	3.50	3.60	3.70
Q	2.20	2.40	2.60

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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